

Please cancel claims 11-17 without any disclaimer or a prejudice to and add new claim 18

as follows:

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18. (New) An apparatus for depositing a layer on a substrate, comprising:

a load lock chamber that receives a substrate;

a preheat chamber that heats the substrate before deposition;

a chemical vapor deposition chamber that deposits thin layers by a chemical vapor deposition method; and

a process chamber that deposits a metal layer on the substrate by a sputtering method,

wherein the substrate is transferred among the chambers in a vacuum while not exposed to ambient atmosphere.

19. (New) The apparatus of claim 18, wherein the substrate is first placed in the load lock chamber and moved into the preheat chamber for preheating.

20. (New) The apparatus of claim 19, wherein the substrate is then moved to the chemical vapor deposition chamber for deposition of silicon.

21. (New) The apparatus of claim 20, wherein the substrate is then moved to the process chamber to deposit metal layer on the substrate by sputtering.